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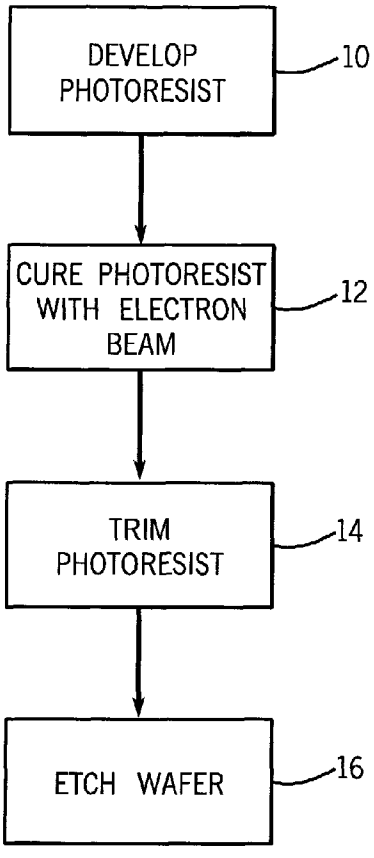
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(54) Title: METHOD OF FORMING ENHANCED TRANSISTOR GATE USING E-BEAM RADIATION AND INTEGRATED CIRCUIT INCLUDING THIS TRANSISTOR GATE



(57) Abstract: A process for forming a transistor (22, 32) having a gate width of less than 70mm is disclosed herein. The process includes E-beam radiation (12) a gate patterned (26, 36) on a photoresist layer, trimming (14) the gate patterned (26, 36) on the photoresist layer, and etching the gate patterned on the photoresist layer to a polysilicon layer (40) disposed below the photoresist layer. The gate pattern is E-beam eradiated by an electron beam.

WO 02/078095 A3

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